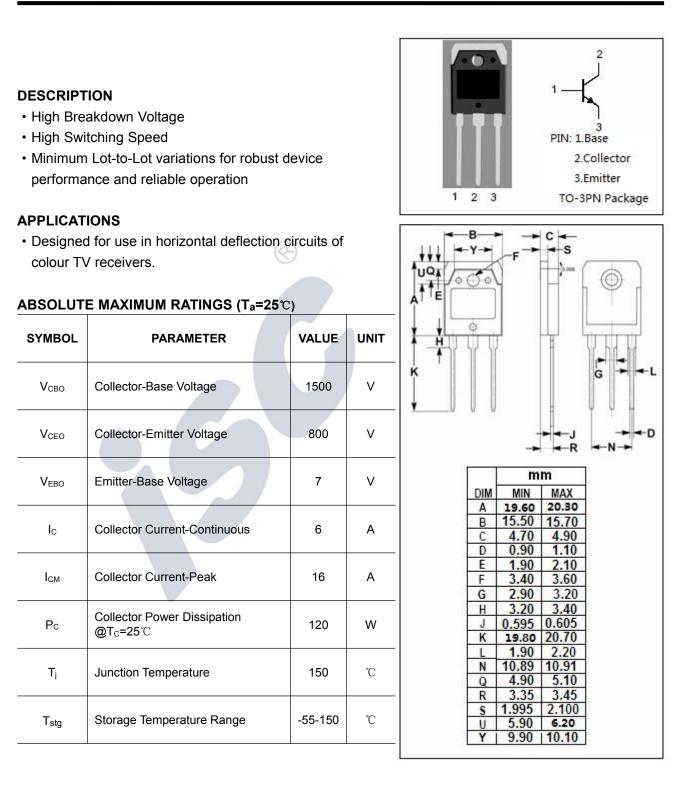


INCHANGE SEMICONDUCTOR

isc Silicon NPN Power Transistor

2SD1403





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2SD1403

ELECTRICAL CHARACTERISTICS

$T_{c}\text{=}25^{\circ}\!\!\!\mathrm{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	ТҮР	МАХ	UNIT
V _{(BR)CBO}	Collector-Base Breakdown Voltage	I _C = 1mA; I _E = 0	1500			V
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	Ic= 30mA; R _{BE} = ∞	800			V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	Ι _Ε = 1mA; Ι _C = 0	7			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = 5Α; I _B = 1Α			5.0	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	I _C = 5Α; I _B = 1Α			1.5	V
I _{CBO}	Collector Cutoff Current	V _{CB} = 800V; I _E = 0			10	μ Α
І _{ЕВО}	Emitter Cutoff Current	V _{ЕВ} = 5V; Ic= 0			1	mA
h _{FE}	DC Current Gain	Ic= 1A ; Vce= 5V	8			



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